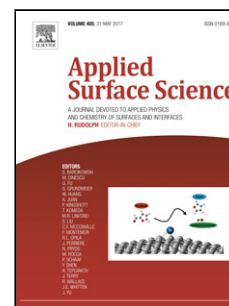


## Accepted Manuscript

Title: Front and back side SIMS analysis of boron-doped delta-layer in diamond

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PII: S0169-4332(17)30778-X  
 DOI: <http://dx.doi.org/doi:10.1016/j.apsusc.2017.03.118>  
 Reference: APSUSC 35494

To appear in: *APSUSC*

Received date: 28-10-2016  
Revised date: 14-2-2017  
Accepted date: 13-3-2017

Please cite this article as: M.-A. Pinault-Thaury, F. Jomard, C. Mer-Calfati, N. Tranchant, M. Pomorski, P. Bergonzo, J.-C. Arnault, Front and back side SIMS analysis of boron-doped delta-layer in diamond, *Applied Surface Science* (2017), <http://dx.doi.org/10.1016/j.apsusc.2017.03.118>

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# Front and back side SIMS analysis of boron-doped delta-layer in diamond

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